

Silicon NPN Power Transistors

2SC2073

DESCRIPTION

- With TO-220 package
- Complement to type 2SA940

APPLICATIONS

- Power amplifier applications
- Vertical output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

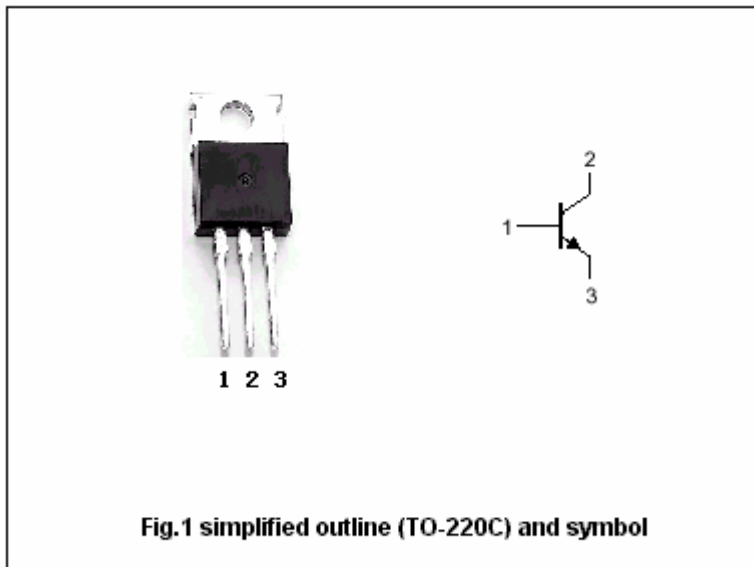


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	150	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.5	A
I _B	Base current		0.5	A
P _C	Collector power dissipation	T _a =25°C	1.5	W
		T _C =25°C	25	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5A I _B =50m A			1.5	V
V _{BE}	Base-emitter on voltage	I _C =0.5A ; V _{CE} =10V			0.85	V
I _{CBO}	Collector cut-off current	V _{CB} =120V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =10V	40		140	
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		35		pF
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		4		MHz

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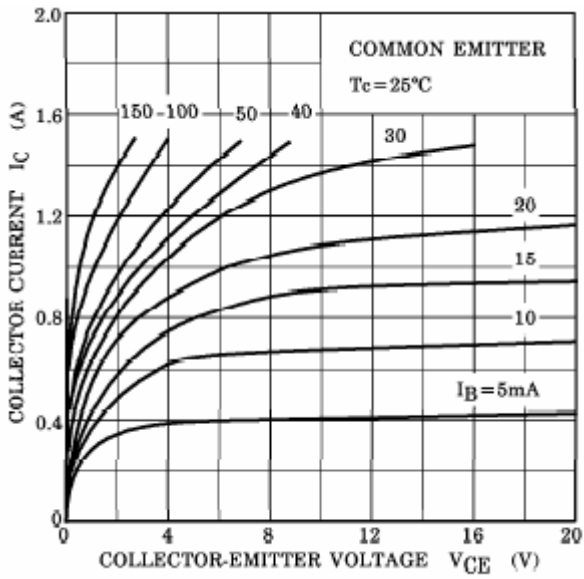


Fig.3 Static Characteristic

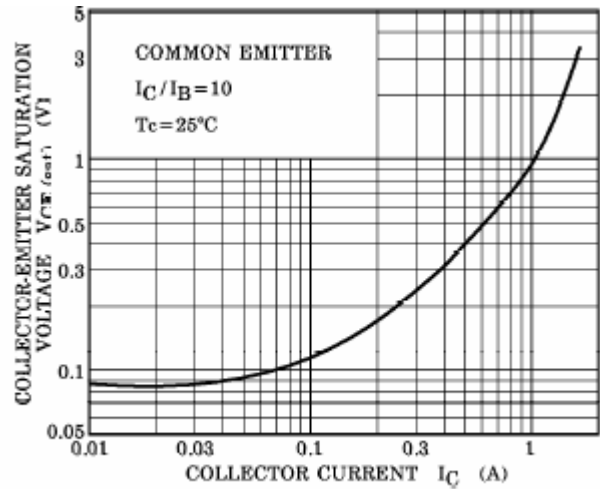


Fig.4 Collector-Emitter Saturation Voltage

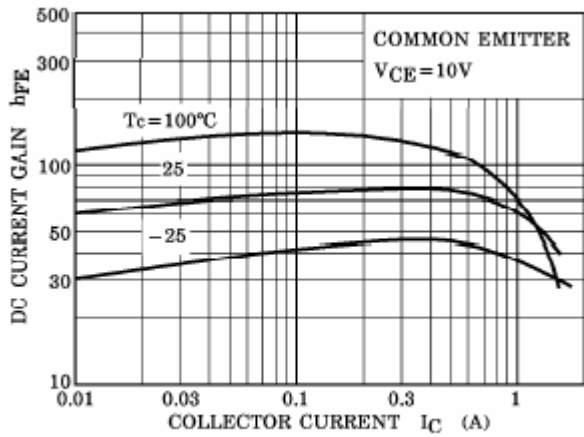


Fig.5 DC current Gain

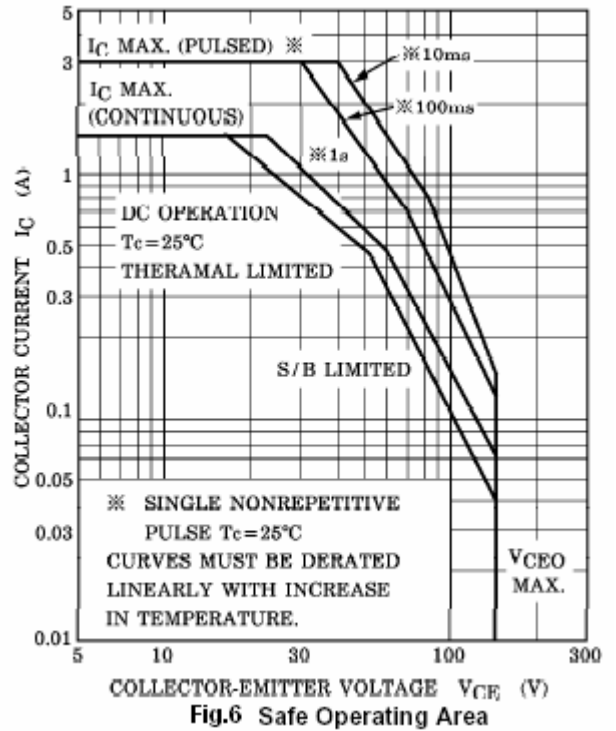


Fig.6 Safe Operating Area